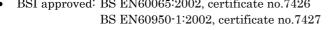
TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

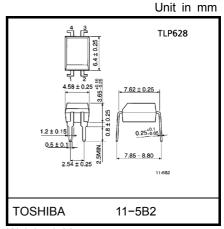
## TLP628,TLP628-2,TLP628-4

# Programmable Controllers DC-Output Module Telecommunication

The TOSHIBA TLP628, -2, and -4 consists of a gallium arsenide infrared emitting diode optically coupled to a phototransistor which has a 350V high voltage of collector—emitter breakdown voltage. The TLP628–2 offers two isolated channels in a eight lead plastic DIP package, while the TLP628–4 provide four isolated channels per package.

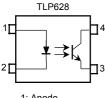
- Collector-emitter voltage: 350 V (min.)
- Current transfer ratio: 50% (min.)
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file No. E67349
  BSI approved: BS EN60065:2002, certificate no.7426



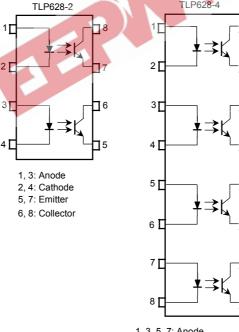


Weight: 0.26g

### Pin Configurations (top view)



- 1: Anode
- 2: Cathode
- 3: Emitter
- 4: Collector

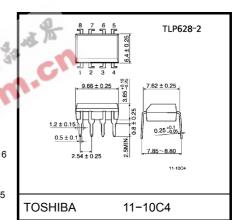


1, 3, 5, 7: Anode 2 4 6 8: Cathode

2, 4, 6, 8: Cathode

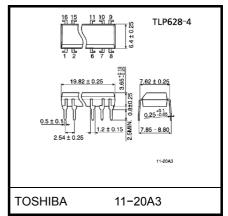
9, 11, 13, 15: Emitter

10, 12, 14, 16: Collector



Weight: 0.54g

**T**12



Weight: 1.1g



#### Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Ra		
		Symbol	TLP628	TLP628-2 TLP628-4	Unit
	Forward current	lF	60	50	mA
	Forward current derating	ΔI <sub>F</sub> / °C	–0.7 (Ta ≥ 39°C)	–0.5 (Ta ≥ 25°C)	mA / °C
LED	Pulse forward current	I <sub>FP</sub>	1 (100µs pu	Α	
	Reverse voltage	$V_{R}$	Į.	V	
	Junction temperature	Tj	12	°C	
	Collector-emitter voltage	V <sub>CEO</sub>	35	50	V
	Emitter-collector voltage	V <sub>ECO</sub>	-	V	
tor	Collector current	IC	50		mA
Detector	Collector power dissipation (1 circuit)	PC	150	100	mW
	Collector power dissipation derating (Ta ≥ 25°C, 1 circuit)	ΔP <sub>C</sub> / °C	-1.5	-1.0	mW / °C
	Junction temperature	Tj	12	°C	
Sto	rage temperature range	T <sub>stg</sub>	<b>−55~125</b>		°C
Оре	erating temperature range	T <sub>opr</sub>	<b>−55~100</b>		°C
Lead soldering temperature		T <sub>sol</sub>	260 (10s)		°C
Total package power dissipation (1 circuit)		PT	200	150	mW
Total package power dissipation derating (Ta ≥ 25°C, 1 circuit)		ΔP <sub>T</sub> / °C	-2.0	-1.5	mW/°C
Isolation voltage		BVS	5000 (AC, 1mii	n., R.H. ≤ 60%) (Note 1)	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>CC</sub>	_	_	200	V
Forward current	lF	_	16	25	mA
Collector current	IC	_	_	10	mA
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



## Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μΑ
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	_	30	_	pF
Detector	Collector–emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.1 mA	350	_	-	٧
	Emitter-collector breakdown voltage	V <sub>(BR)</sub> ECO	I <sub>E</sub> = 0.1 mA	7	_	_	V
	Collector dark current	lono	V <sub>CE</sub> = 300 V	_	10	200	nA
	Collector dark current	ICEO	V <sub>CE</sub> = 300 V, Ta = 85°C	_	_	50	μΑ
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0, f = 1 MHz	_	10	_	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V Rank GB	50	_	600	- %
			100	_	600	
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	IF = 1 mA, V <sub>CE</sub> = 0.4 V Rank GB		60	1	- %
			30	_	1	70
		I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = 8 mA	ı	_	0.4	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$	1	0.2	ı	V
		Rank GB	ı	_	0.4	

## Isolation Characteristics (Ta = 25°C)

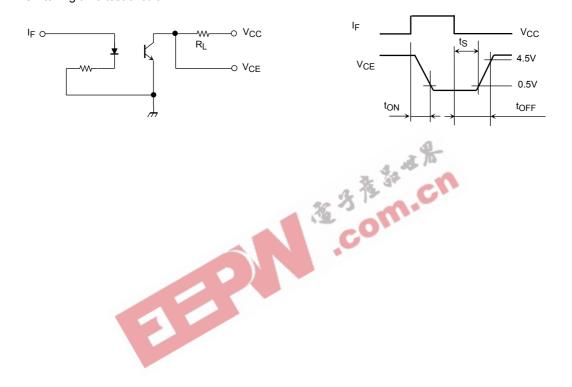
Characteristic	1	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output		CS	V <sub>S</sub> = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance		R <sub>S</sub>	V <sub>S</sub> = 500 V R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage			AC, 1 minute	5000	_	_	- V <sub>rms</sub>
		BVS	AC, 1 second, in oil	_	10000	_	
			DC, 1 minute, in oil	_	10000	_	V <sub>dc</sub>

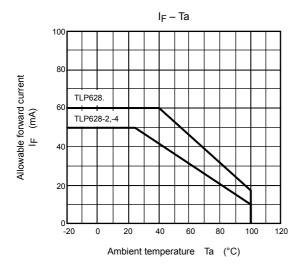


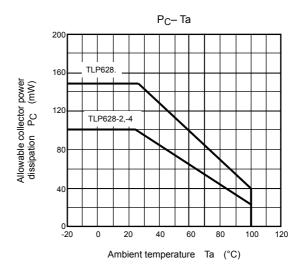
#### **Switching Characteristics (Ta = 25°C)**

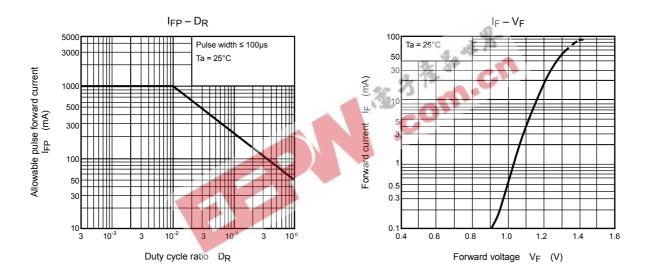
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t <sub>r</sub>		_	2	_	- µs
Fall time	t <sub>f</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA	_	3	_	
Turn-on time	t <sub>on</sub>	AR <sub>L</sub> = 100Ω	_	3	_	
Turn-off time	t <sub>off</sub>		_	3	_	
Turn-on time	ton	$R_L$ = 1.9 kΩ (Fig.1) $V_{CC}$ = 5 V, $I_F$ = 16 mA	_	3	_	
Storage time	t <sub>S</sub>		_	40	_	μs
Turn-off time	tOFF		_	90	_	

Fig. 1 Switching time test circuit

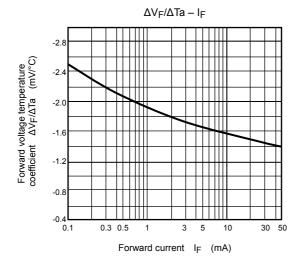


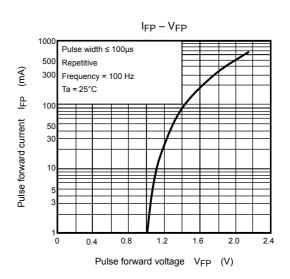


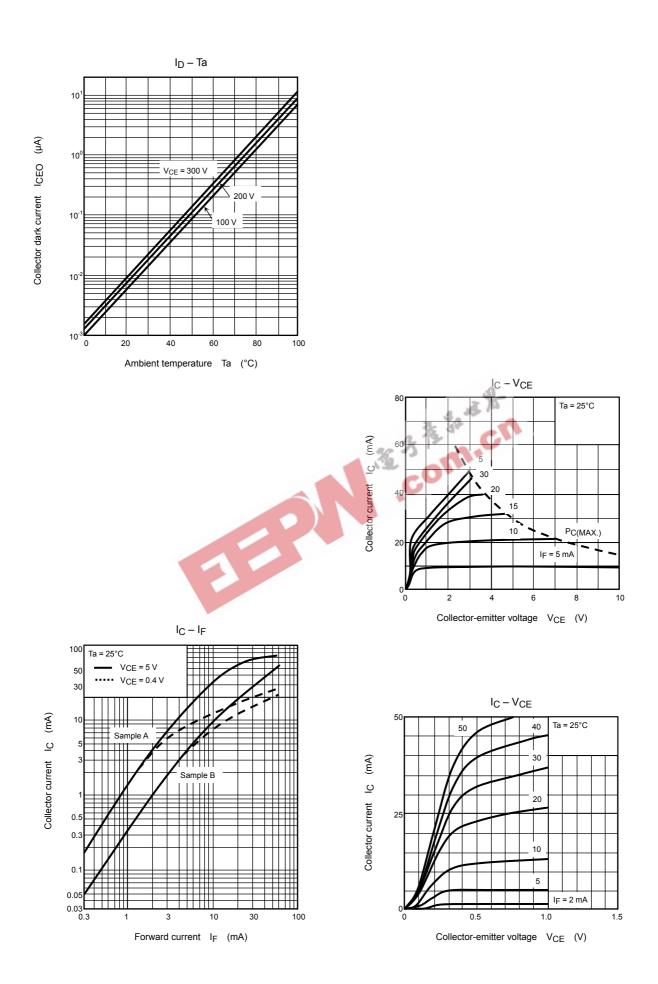


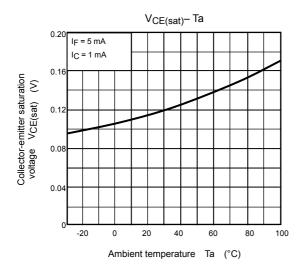


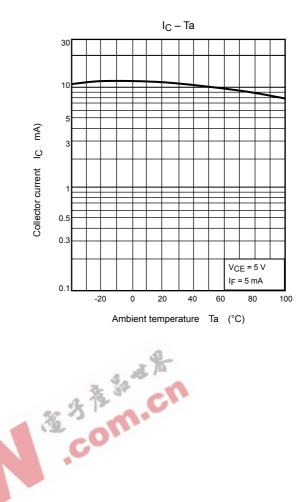
5

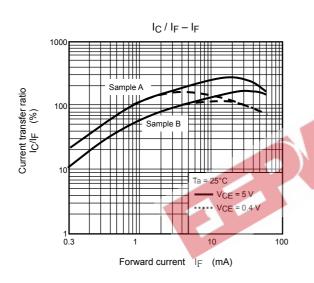


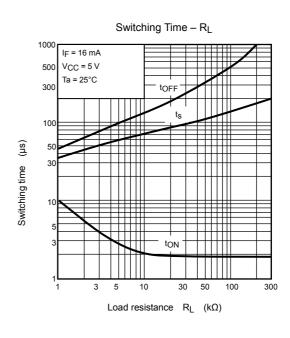












#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patents or other rights of
  TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.